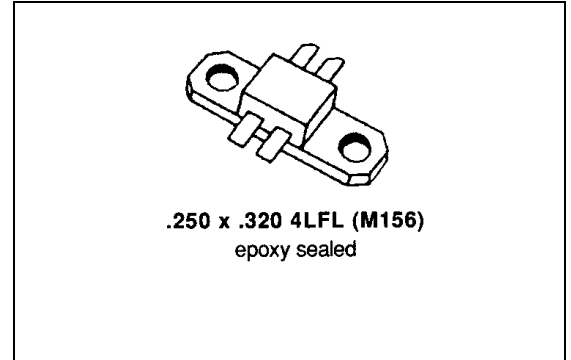


# MS1452

## RF & MICROWAVE TRANSISTORS 800-900 MHz BASE STATION APPLICATIONS

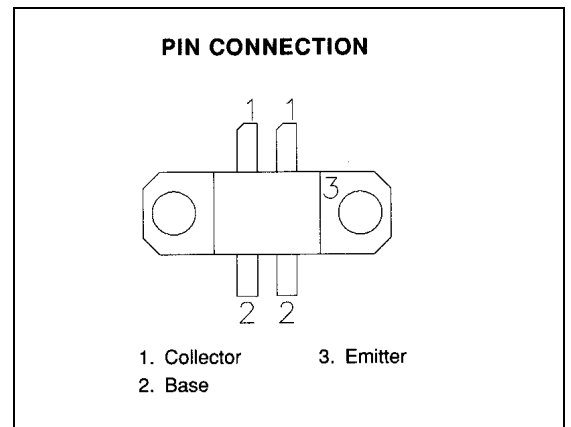
### Features

- 800-900 MHz
- 24 VOLTS
- COMMON EMITTER
- GOLD METALLIZATION
- INTERNAL INPUT MATCHING
- CLASS AB LINEAR OPERATION
- $P_{OUT} = 30$  W MINIMUM
- $G_P = 7.5$  dB



### DESCRIPTION:

The MS1452 is a gold metallized epitaxial silicon NPN planar transistor using diffused emitter ballast resistors for high linearity Class AB operation in cellular base station application.



### ABSOLUTE MAXIMUM RATINGS (T<sub>case</sub> = 25°C)

Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector-Base Voltage	48	V
V <sub>CES</sub>	Collector-Emitter Voltage	45	V
V <sub>EBO</sub>	Emitter-Base Voltage	4.0	V
P <sub>DISS</sub>	Power Dissipation	43	W
I <sub>C</sub>	Device Current	5	A
T <sub>J</sub>	Junction Temperature	+200	°C
T <sub>STG</sub>	Storage Temperature	-65 to +150	°C

### Thermal Data

R <sub>TH(J-C)</sub>	Thermal Resistance Junction-case	3.0	°C/W
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## ELECTRICAL SPECIFICATIONS (T<sub>case</sub> = 25°C)

### STATIC

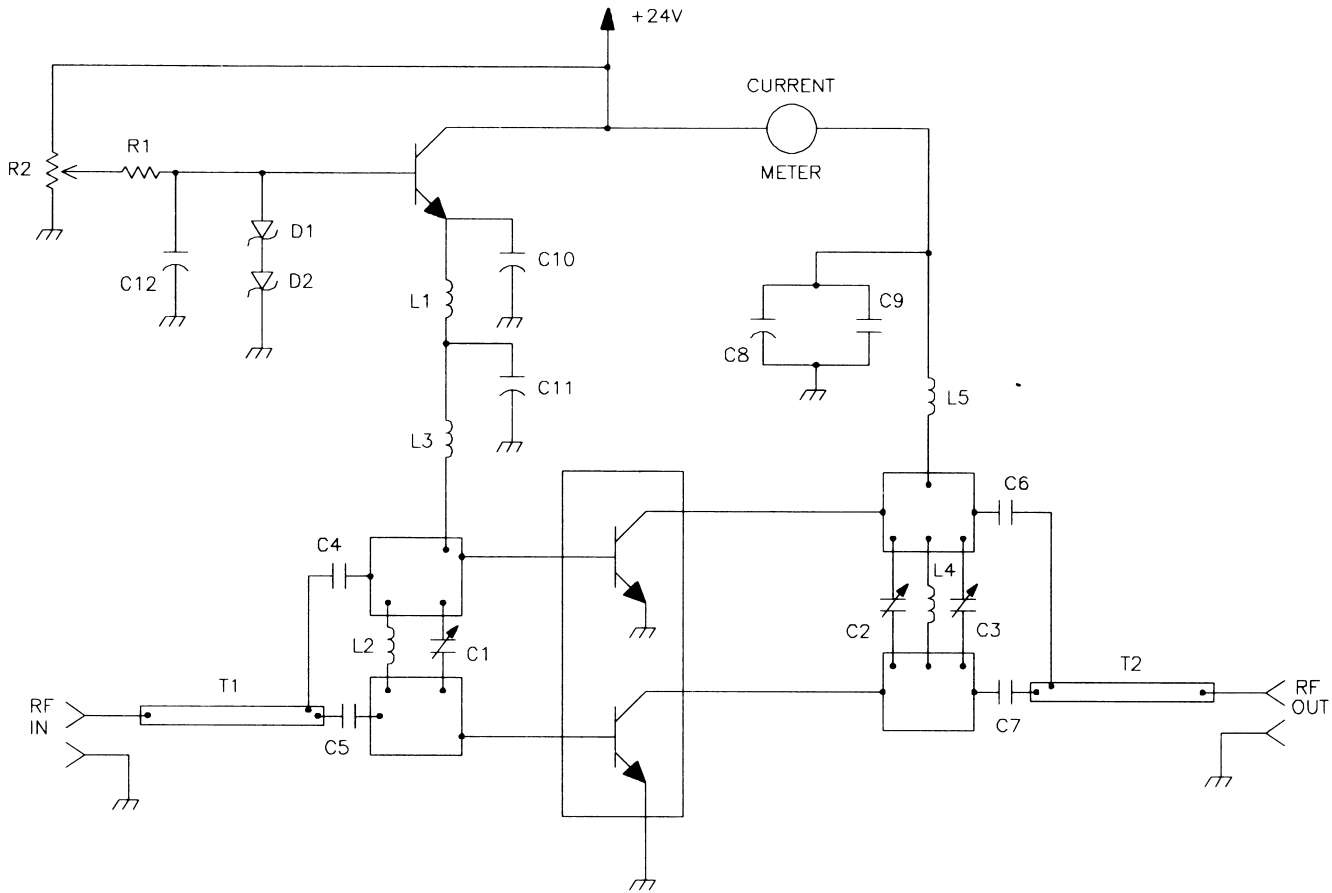
Symbol	Test Conditions		Value			Unit
			Min.	Typ.	Max.	
<b>BV<sub>CBO</sub></b>	<b>I<sub>C</sub> = 50 mA</b>	<b>I<sub>E</sub> = 0 mA</b>	<b>48</b>	<b>50</b>	<b>---</b>	<b>V</b>
<b>BV<sub>CEO</sub></b>	<b>I<sub>C</sub> = 20 mA</b>	<b>I<sub>B</sub> = 0 mA</b>	<b>25</b>	<b>30</b>	<b>---</b>	<b>V</b>
<b>BV<sub>EBO</sub></b>	<b>I<sub>E</sub> = 5 mA</b>	<b>I<sub>C</sub> = 0 mA</b>	<b>3.5</b>	<b>4.0</b>	<b>---</b>	<b>V</b>
<b>I<sub>CBO</sub></b>	<b>V<sub>CB</sub> = 24 V</b>	<b>I<sub>E</sub> = 0 mA</b>	<b>---</b>	<b>---</b>	<b>1.0</b>	<b>mA</b>
<b>HFE</b>	<b>V<sub>CE</sub> = 5 V</b>	<b>I<sub>C</sub> = 100mA</b>	<b>20</b>	<b>---</b>	<b>100</b>	<b>---</b>

### DYNAMIC

Symbol	Test Conditions			Value			Unit
				Min.	Typ.	Max.	
<b>P<sub>OUT</sub></b>	<b>f = 960 MHz</b>	<b>P<sub>IN</sub> = 5.3 W</b>	<b>V<sub>CC</sub> = 24V</b>	<b>30</b>	<b>---</b>	<b>---</b>	<b>W</b>
<b>G<sub>P</sub></b>	<b>f = 960 MHz</b>	<b>P<sub>IN</sub> = 5.3 W</b>	<b>V<sub>CC</sub> = 24V</b>	<b>7.5</b>	<b>---</b>	<b>---</b>	<b>dB</b>
<b>η<sub>C</sub></b>	<b>f = 960 MHz</b>	<b>P<sub>IN</sub> = 5.3 W</b>	<b>V<sub>CC</sub> = 24V</b>	<b>45</b>	<b>50</b>	<b>---</b>	<b>%</b>
<b>C<sub>OB</sub></b>	<b>f = 1 MHz</b>	<b>V<sub>CB</sub> = 24V</b>		<b>---</b>	<b>20</b>	<b>24</b>	<b>pF</b>

Conditions: I<sub>CQ</sub> = 150 mA

**TEST CIRCUIT**



- C1, C2,
- C3 : 0.8 - 8pF Variable Capacitors
- C4, C5,
- C6, C7 : 62pF
- C8 : 22 $\mu$ F
- C9 : 180pF
- C10 : 47 $\mu$ F, 63V
- C11 : 180pF
- C12 : 10 $\mu$ F, 63V

D1, D2 : SD1423 Devices

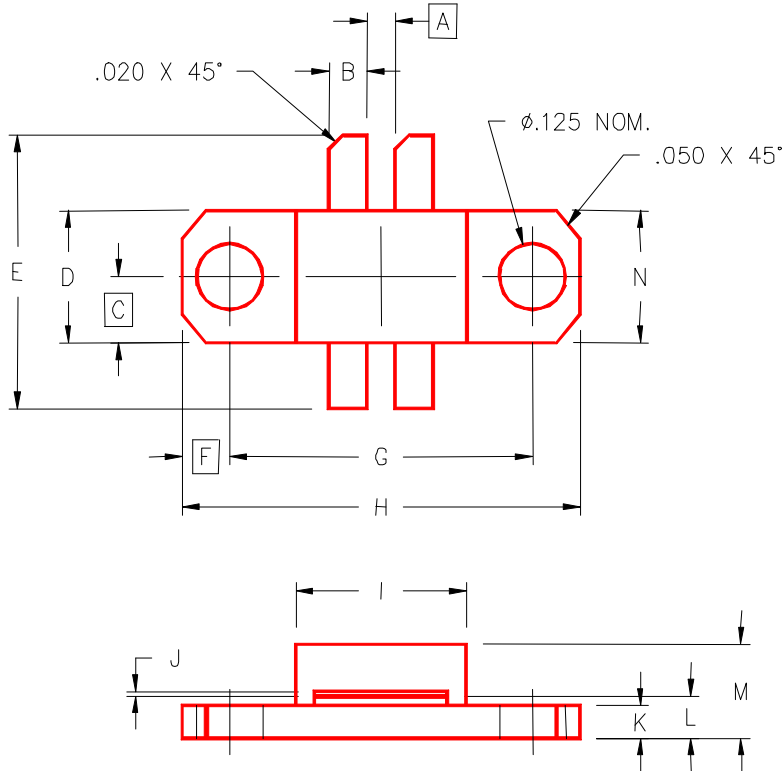
- L1, L2 : #22 AWG with Ferrite Core
- L3 : 4 Turns, #22 AWG
- L4 : 2 Turns, #22 AWG
- L5 : 5 Turns, #22 AWG

T1, T2 :  $\lambda/4$  Transformers

Material: Epsilam 10, Er = 10.5, Height = .050"

**PACKAGE MECHANICAL DATA**

PACKAGE STYLE M156



	MINIMUM INCHES/MM	MAXIMUM INCHES/MM		MINIMUM INCHES/MM	MAXIMUM INCHES/MM
A	.060/1,52		I	.315/8,00	.325/8,26
B	.055/1,40	.065/1,65	J	.002/0,05	.006/0,15
C	.124/3,15		K	.055/1,40	.065/1,65
D	.243/6,17	.253/6,43	L	.075/1,91	.095/2,41
E	.635/16,13	.665/16,89	M		.190/4,83
F	.092/2,34		N	.245/6,22	.255/6,48
G	.555/14,10	.565/14,35			
H	.739/18,77	.749/19,02			